



DGD2190

HIGH-SIDE AND LOW-SIDE GATE DRIVER IN SO-8

Description

The DGD2190 is a high voltage/high speed gate driver capable of driving N-Channel MOSFETs and IGBTs in a half bridge configuration. High voltage processing techniques enable the DGD2190's high-side to switch to 600V in a bootstrap operation under high dV/dt conditions.

The DGD2190 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) for easy interfacing with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction.

The DGD2190 is offered in the SO-8 package and operates over an extended -40°C to +125°C temperature range.

Applications

- DC-DC Converters
- DC-AC Inverters
- AC-DC Power Supplies
- Motor Controls
- Class D Power Amplifiers

HIN COM LIN DGD2190 Vs LO VCC

Typical Configuration

Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in a Half-Bridge Configuation
- Output Drivers Capable of 4.5A/4.5A Typ Sink/Source
- Logic Input (HIN and LIN) 3.3V Capability
- Schmitt Triggered Logic Inputs with Internal Pull-Down
- Undervoltage Lockout for High and Low-Side Drivers
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SO-8 (Type TH)
 - Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.075 grams (Approximate)



SO-8 Top View

Ordering Information (Note 4)

Part Number		Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	DGD2190S8-13	DGD2190	13	12	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

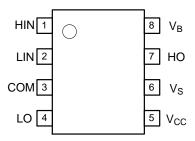
Marking Information



);; = Manufacturer's marking DGD2190 = Product Type Marking Code YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



Pin Diagrams

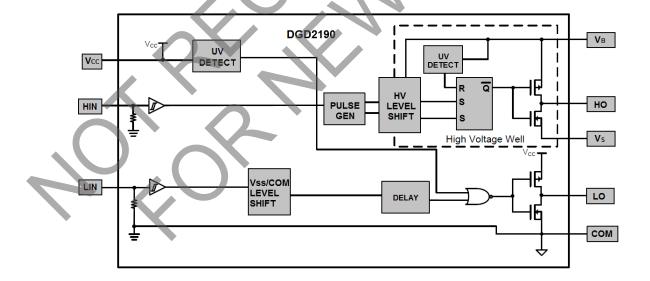


Top View: SO-8

Pin Descriptions

Pin Number	Pin Name	Function
1	HIN	Logic Input for High-side Gate Driver Output, in Phase with HO
2	LIN	Logic Input for Low-side Gate Driver Output, in Phase with LO
3	COM	Low-Side and Logic Return
4	LO	Low-Side Gate Drive Output
5	Vcc	Low-Side and Logic Fixed Supply
6	Vs	High-Side Floating Supply Return
7	НО	High-Side Gate Drive Output
8	V _B	High-Side Floating Supply

Functional Block Diagram





DGD2190

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-side Floating Supply Voltage	V _B	-0.3 to +624	V
High-side Floating Supply Offset Voltage	Vs	V _B -24 to V _B +0.3	V
High-side Floating Output Voltage	V_{HO} V_{S} -0.3 to V_{B} +0.3		V
Offset Supply Voltage Transient	dV _S / dt	50	V/ns
Low-side and Logic Fixed Supply Voltage	Vcc	-0.3 to +24	V
Low-side Output Voltage	V _{LO}	-0.3 to V _{CC} +0.3	V
Logic Input Voltage (HIN and LIN)	VIN	-0.3 to V _{CC} +0.3	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P _D	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	200	°C/W
Thermal Resistance, Junction to Case (Note 5)	Rejc	45	°C/W
Operating Temperature	TJ	+150	°C
Storage Temperature Range	T _{STG}	-55 to +150	C

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High-side Floating Supply Absolute Voltage	V _B	Vs +10	V _S +20	V
High-side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High-side Floating Output Voltage	V _{HO}	Vs	V_{B}	V
Low-side Fixed Supply Voltage	Vcc	10	20	V
Low-side Output Voltage	V _{LO}	0	V _{CC}	V
Logic Input Voltage (HIN and LIN)	V _{IN}	0	5	V
Ambient Temperature	T _A	-40	+125	°C

Notes:

- 5. When mounted on a standard JEDEC 2-layer FR-4 board.
- 6. Logic operation for Vs of -5V to +600V.

DGD2190 Document Number DS38327 Rev. 6 - 3



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$\textbf{DC Electrical Characteristics} \ (V_{BIAS} \ (V_{CC}, V_{BS}) = 15V, \ @T_A = +25^{\circ}C, \ unless \ otherwise \ specified.) \ (Note \ 7)$

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Logic "1" Input Voltage (Note 8)	V_{IH}	2.5	_	1	V	$V_{CC} = 10V$ to $20V$
Logic "0" Input Voltage (Note 8)	V_{IL}	_	_	0.8	>	V _{CC} = 10V to 20V
High Level Output Voltage, V _{BIAS} - V _O	V _{OH}	_	_	0.1	V	$I_O = 0mA$
Low Level Output Voltage, Vo	V_{OL}	_	_	0.035	V	$I_O = 0mA$
Offset Supply Leakage Current	I_{LK}	_	_	50	μΑ	$V_B = V_S = 600V$
Quiescent V _{BS} Supply Current	I_{BSQ}	_	45	80	μΑ	$V_{IN} = 0V \text{ or } 5V$
Quiescent V _{CC} Supply Current	Iccq	_	75	200	μΑ	$V_{IN} = 0V \text{ or } 5V$
Logic "1" Input Bias Current	I _{IN+}	_	25	50	μA	$V_{IN} = 5V$
Logic "0" Input Bias Current	I _{IN-}	_	1.0	2.0	μΑ	$V_{IN} = 0V$
V _{BS} Supply Undervoltage Positive Going Threshold	V_{BSUV+}	7.6	8.4	9.8	V	
V _{BS} Supply Undervoltage Negative Going Threshold	V _{BSUV} -	6.9	7.8	9.0	V	—
V _{CC} Supply Undervoltage Positive Going Threshold	V _{CCUV+}	7.6	8.4	9.8	V	_
V _{CC} Supply Undervoltage Negative Going Threshold	V _{CCUV} -	6.9	7.8	9.0	V	_
V and V Undervoltage Hyptoresis	Vccuvн	_	0.6	1	V	_
V _{CC} and V _{BS} Undervoltage Hysteresis	V _{BSUVH}	_	0.6		٧	_
Output High Short Circuit Pulsed Current	I _{O+}	3.5	4.5		Α	$V_0 = 0V$, PW ≤ 10 ms
Output Low Short Circuit Pulsed Current	l ₀₋	3.5	4.5		A	V ₀ = 15V, PW ≤ 10ms

Notes:

- 7. The V_{IN} and I_{IN} parameters are applicable to the two logic pins; HIN and LIN. The V_O and I_O parameters are applicable to the respective output pins: HO and LO.
- 8. For optimal operation, it is recommended that the input pulses (HIN and LIN) should have a minimum amplitude of 2.5V with a minimum pulse width of 280ns.

AC Electrical Characteristics (V_{BIAS} (V_{CC} , V_{BS}) = 15V, C_L = 1000pF, @ T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Turn-On Propagation Delay	t _{ON}	-	140	200	ns	$V_S = 0V$
Turn-Off Propagation Delay	toff	-	140	200	ns	$V_S = 0V$
Delay Matching, HO & LO Turn On/Off	t _{DM}	1-1	0	50	ns	_
Turn-On Rise Time	t _R	1-7	25	50	ns	$V_S = 0V$
Turn-Off Fall Time	t _F	1	20	45	ns	$V_S = 0V$



Timing Waveforms

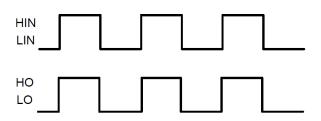


Figure 1. Input / Output Timing Diagram

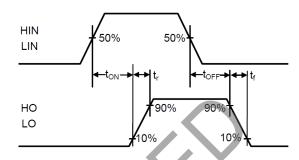


Figure 2. Switching Time Waveform Definitions

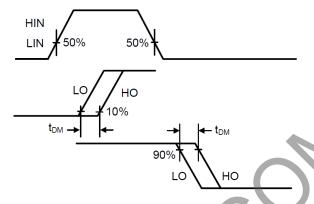


Figure 3. Delay Matching Waveform Definitions





Typical Performance Characteristics (Vcc=15V, @TA = +25°C, unless otherwise specified.)

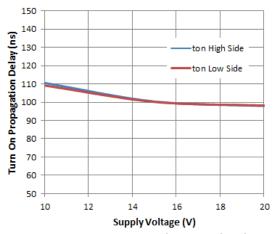


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

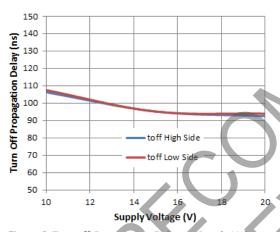


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

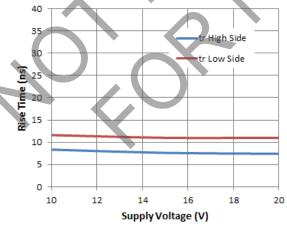


Figure 8. Rise Time vs. Supply Voltage

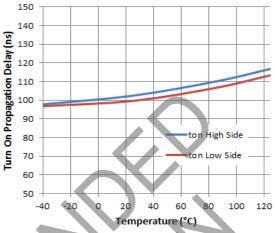


Figure 5. Turn-on Propagation Delayvs. Temperature

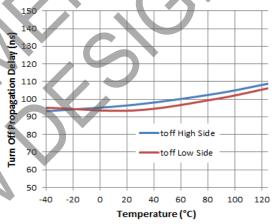


Figure 7. Turn-off Propagation Delay vs. Temperature

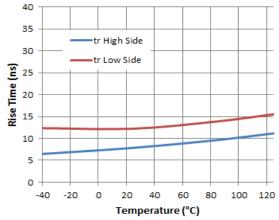


Figure 9. Rise Time vs. Temperature



Typical Performance Characteristics (continued) (@TA = +25°C, unless otherwise specified.)

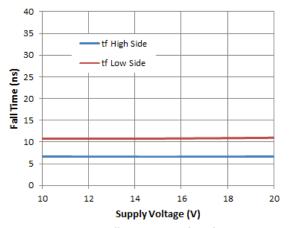


Figure 10. Fall Time vs. Supply Voltage

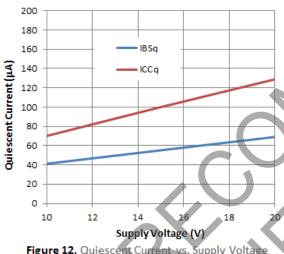


Figure 12. Quiescent Current vs. Supply Voltage

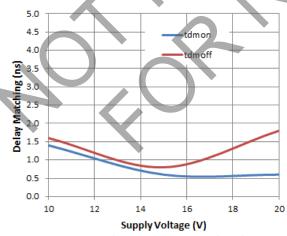


Figure 14. Delay Matching vs. Supply Voltage

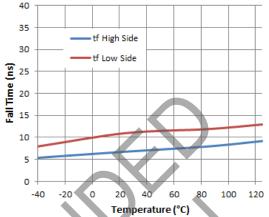


Figure 11. Fall Time vs. Temperature

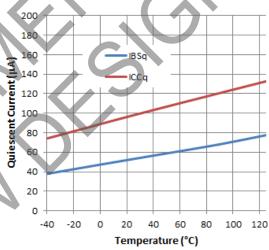


Figure 13. Quiescent Current vs. Temperature

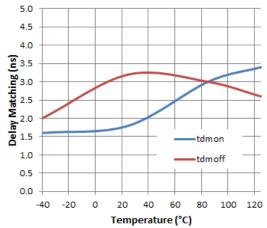


Figure 15. Delay Matching vs. Temperature



Typical Performance Characteristics (continued) (@T_A = +25°C, unless otherwise specified.)

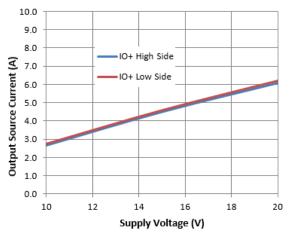


Figure 16. Output Source Current vs. Supply Voltage

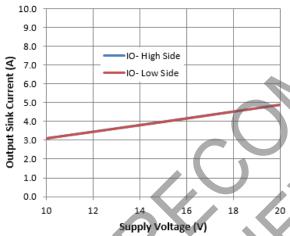


Figure 18. Output Sink Current vs. Supply Voltage

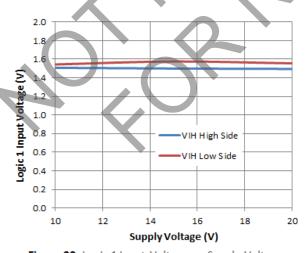


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

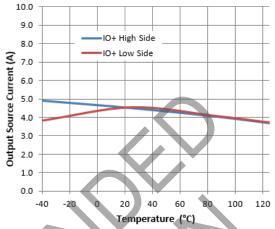


Figure 17. Output Source Current vs. Temperature

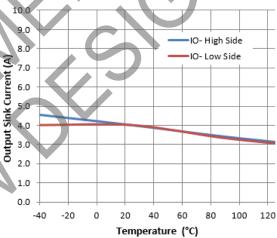


Figure 19. Output Sink Current vs. Temperature

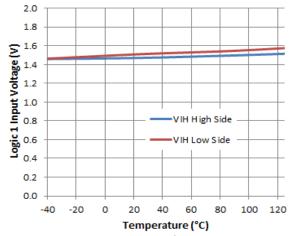


Figure 21. Logic 1 Input Voltage vs. Temperature



Typical Performance Characteristics (continued) (@T_A = +25°C, unless otherwise specified.)

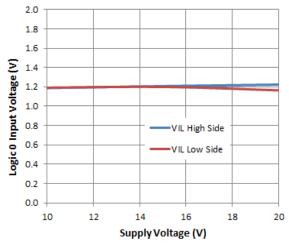
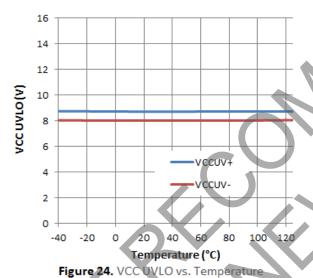


Figure 22. Logic O Input Voltage vs. Supply Voltage



20.0 OffsetSupply Leakage Current (μΑ) 18.0 16.0 12.0 10.0 8.0 6.0 4.0 2.0 0.0 -40 -20 40 60 80 100 Temperature (°C)

Figure 26. Offset Supply Leakage Current vs. Temperature

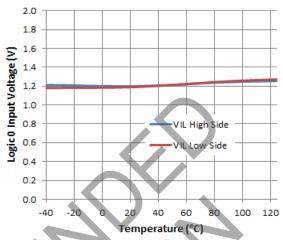


Figure 23. Logic 0 Input Voltage vs. Temperature

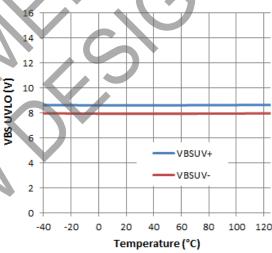


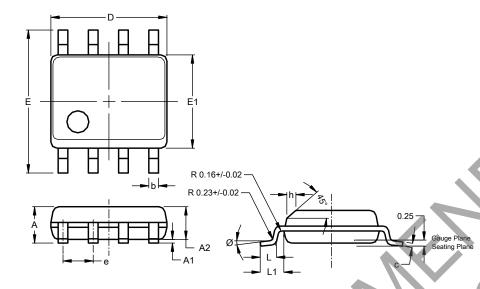
Figure 25. VBS UVLO vs. Temperature



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8 (Type TH)

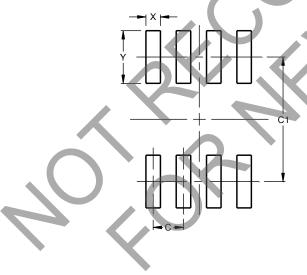


SO-8 (Type TH)					
Dim	Min	Max	Тур		
Α	1.35	1.75	_		
A1	0.10	0.25	_		
A2	-	/ –	1.45		
b	0.35	0.51	_		
C	0.190	0.248	_		
ρ	4.80	5.00	4.90		
E	5.80	6.20	6.00		
E1	3.80	4.00	3.90		
е	`	-	1.27		
h	0.25	0.50	_		
_	0.41	1.27	_		
1	1	1	1.04		
Ø	0°	8°	_		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8 (Type TH)



Dimensions	Value (in mm)
С	1.27
C1	5.20
Х	0.60
Υ	2 20

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



DGD2190

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